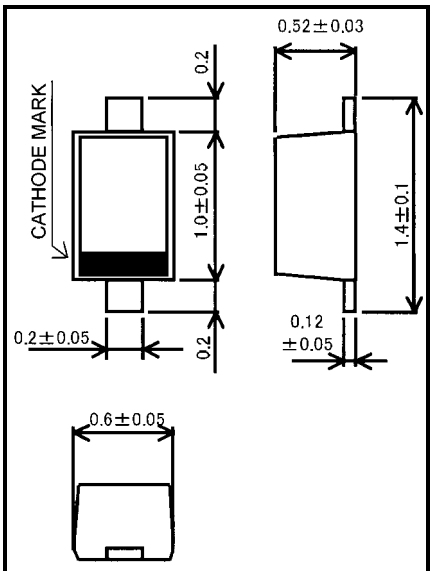
TOSHIBA Diode Silicon Epitaxial Pin Type

J D P 2 S 0 2 S

UHF~VHF Band RF Attenuator Applications

- Suitable for reducing set's size as a result from enabling high-density mounting due to 2-pin small packages.
- Low series resistance: r_S = 1.0 Ω (typ.)
- Low capacitance: C_T = 0.3 pF (typ.)

Unit in mm



sESC	
JEDEC	—
EIAJ	—
TOSHIBA	1-1K1A

Weight: 0.0011 g

Maximum Ratings (Ta = 25°C)

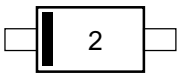
Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	30	V
Forward current	I_F	50	mA
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55~150	°C

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	I_R = 10 μA	30	—	—	V
Reverse current	I_R	V_R = 30 V	—	—	0.1	μA
Forward voltage	V_F	I_F = 50 mA	—	0.9	0.94	V
Capacitance	C_T	V_R = 1 V, f = 1 MHz	—	0.3	0.5	pF
Series resistance	r_s	I_F = 10 mA, f = 100 MHz	—	1.0	1.5	Ω

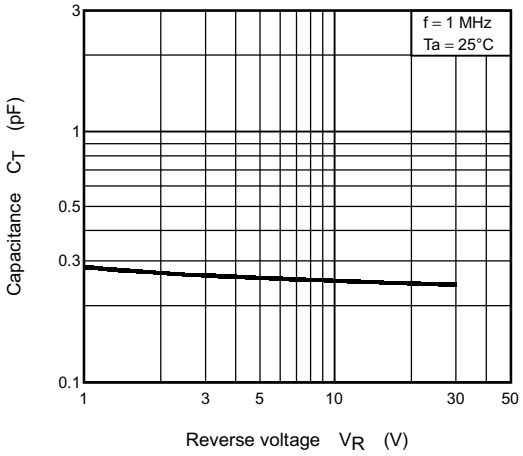
Note: Signal level when capacitance is measured. V_{sig} = 20 mVrms

Marking

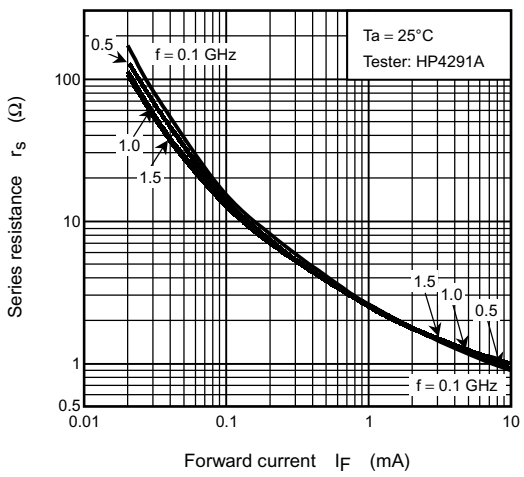


000707EAA2

$C_T - V_R$



$r_s - I_F$



000707EAA2

- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.